

NTP10N60, NTB10N60

Preferred Devices

Advance Information

Power MOSFET 10 Amps, 600 Volts N-Channel TO-220 and D²PAK

Designed for high voltage, high speed switching applications in power supplies, converters, power motor controls and bridge circuits.

Features

- Higher Current Rating
- Lower $R_{DS(on)}$
- Lower Capacitances
- Lower Total Gate Charge
- Tighter V_{SD} Specifications
- Avalanche Energy Specified

Typical Applications

- Switch Mode Power Supplies
- PWM Motor Controls
- Converters
- Bridge Circuits

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	600	Vdc
Drain-Gate Voltage ($R_{GS} = 1.0\text{ M}\Omega$)	V_{DGR}	600	Vdc
Gate-Source Voltage	V_{GS}	± 20	Vdc
– Continuous	V_{GSM}	± 40	
– Non-Repetitive ($t_p \leq 10\text{ ms}$)			
Drain-Continuous	I_D	10	Adc
– Continuous @ 100°C	I_D	8.0	
– Single Pulse ($t_p \leq 10\text{ }\mu\text{s}$)	I_{DM}	35	
Total Power Dissipation	P_D	201	Watts
Derate above 25°C		1.61	W/ $^\circ\text{C}$
Operating and Storage	T_J, T_{stg}	-55 to $+150$	$^\circ\text{C}$
Temperature Range			
Single Drain-to-Source Avalanche	E_{AS}	500	mJ
Energy – Starting $T_J = 25^\circ\text{C}$ ($V_{DD} = 100\text{ V}$, $V_{GS} = 10\text{ Vdc}$, $I_L = 10\text{ A}$, $L = 10\text{ mH}$, $R_G = 25\text{ }\Omega$)			
Thermal Resistance	$R_{\theta JC}$	0.62	$^\circ\text{C/W}$
– Junction-to-Case	$R_{\theta JA}$	62.5	
– Junction-to-Ambient	$R_{\theta JA}$	50	
– Junction-to-Ambient (Note 1.)			
Maximum Lead Temperature for	T_L	260	$^\circ\text{C}$
Soldering Purposes, 1/8" from case			
for 10 seconds			

1. When surface mounted to an FR4 board using the minimum recommended pad size.

This document contains information on a new product. Specifications and information herein are subject to change without notice.



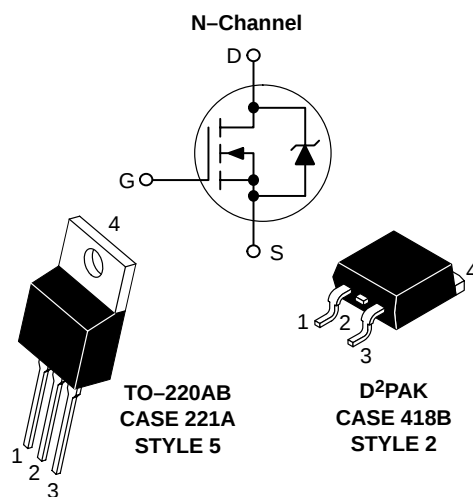
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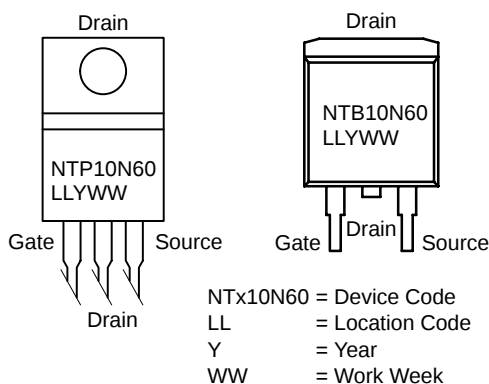
10 AMPERES

600 VOLTS

$R_{DS(on)} = 0.75\text{ }\Omega$



MARKING DIAGRAMS AND PIN ASSIGNMENTS



ORDERING INFORMATION

Device	Package	Shipping
NTP10N60	TO-220AB	50 Units/Rail
NTB10N60	D ² PAK	50 Units/Rail
NTB10N60T4	D ² PAK	800/Tape & Reel

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 0.25 mAdc) Temperature Coefficient (Positive)	V _{(BR)DSS}	600 –	– 585	– –	Vdc mV/°C
Zero Gate Voltage Collector Current (V _{DS} = 600 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 600 Vdc, V _{GS} = 0 Vdc, T _J = 125°C)	I _{DSS}	– –	– –	10 100	μAdc
Gate-Body Leakage Current (V _{GS} = ±20 Vdc, V _{DS} = 0)	I _{GSS(f)} I _{GSS(r)}	– –	– –	100 100	nAdc

ON CHARACTERISTICS (Note 1.)

Gate Threshold Voltage I _D = 0.25 mA, V _{DS} = V _{GS} Temperature Coefficient (Negative)	V _{GS(th)}	2.0 –	2.5 5.8	4.0 –	Vdc mV/°C
Static Drain-to-Source On-Resistance (V _{GS} = 10 Vdc, I _D = 5 Adc)	R _{DS(on)}	–	0.6	0.75	Ohm
Drain-to-Source On-Voltage (V _{GS} = 10 Vdc, I _D = 10 Adc) (V _{GS} = 10 Vdc, I _D = 5 Adc, T _J = 125°C)	V _{DS(on)}	– –	– –	9.0 7.9	Vdc
Forward Transconductance (V _{DS} = 8 Vdc, I _D = 5 Adc)	g _{FS}	3.0	10	–	mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	(V _{DS} = 25 Vdc, V _{GS} = 0 Vdc, f = 1.0 MHz)	C _{iss}	–	1840	2580	pF
Output Capacitance		C _{oss}	–	470	660	
Transfer Capacitance		C _{rss}	–	20	40	

SWITCHING CHARACTERISTICS (Note 2.)

Turn-On Delay Time	(V _{DD} = 300 Vdc, I _D = 10 Adc, V _{GS} = 10 Vdc, R _G = 9.1 Ω)	t _{d(on)}	–	11.5	20	ns
Rise Time		t _r	–	20	40	
Turn-Off Delay Time		t _{d(off)}	–	50	100	
Fall Time		t _f	–	30	60	
Gate Charge	(V _{DS} = 400 Vdc, I _D = 10 Adc, V _{GS} = 10 Vdc)	Q _T	–	36	50	nC
		Q ₁	–	8.0	–	
		Q ₂	–	11	–	
		Q ₃	–	20	–	

SOURCE-DRAIN DIODE CHARACTERISTICS

Forward On-Voltage (Note 1.)	(I _S = 10 Adc, V _{GS} = 0 Vdc) (I _S = 10 Adc, V _{GS} = 0 Vdc, T _J = 125°C)	V _{SD}	– –	0.85 0.75	1.0 –	Vdc
Reverse Recovery Time	(I _S = 10 Adc, V _{GS} = 0 Vdc, dis/dt = 100 A/μs)	t _{rr}	–	510	–	ns
		t _a	–	165	–	
		t _b	–	345	–	
Reverse Recovery Stored Charge		Q _{RR}	–	4.1	–	μC

INTERNAL PACKAGE INDUCTANCE

Internal Drain Inductance (Measured from contact screw on tab to center of die) (Measured from the drain lead 0.25" from package to center of die)	L _D	– –	3.5 4.5	– –	nH
Internal Source Inductance (Measured from the source lead 0.25" from package to source bond pad)	L _S	–	7.5	–	

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
2. Switching characteristics are independent of operating junction temperature.

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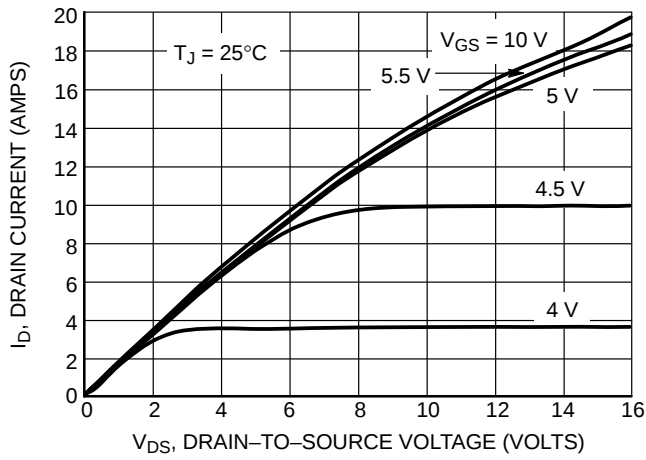


Figure 1. On-Region Characteristics

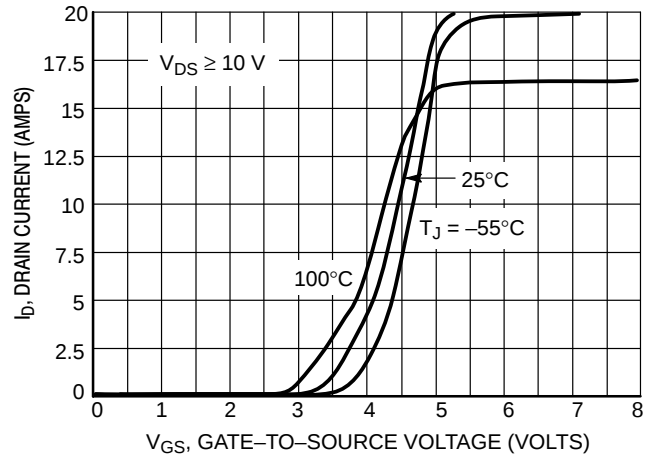


Figure 2. Transfer Characteristics

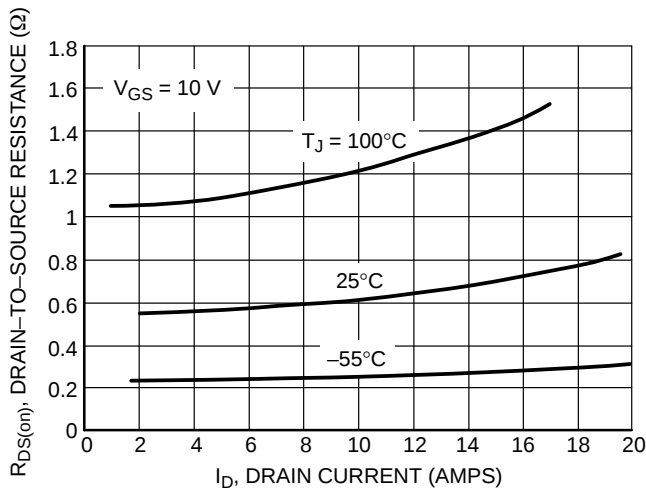


Figure 3. On-Resistance versus Drain Current and Temperature

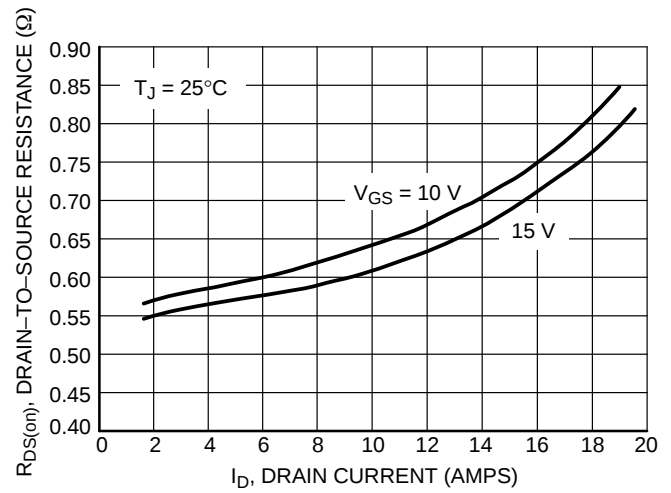


Figure 4. On-Resistance versus Drain Current and Gate Voltage

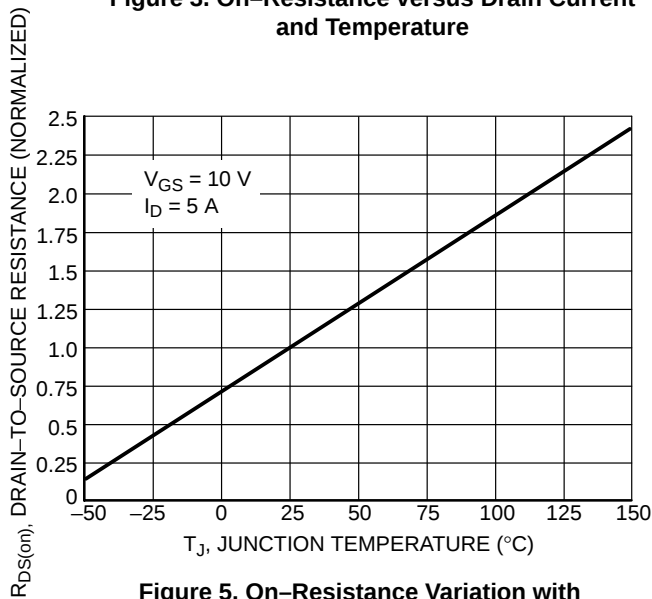


Figure 5. On-Resistance Variation with Temperature

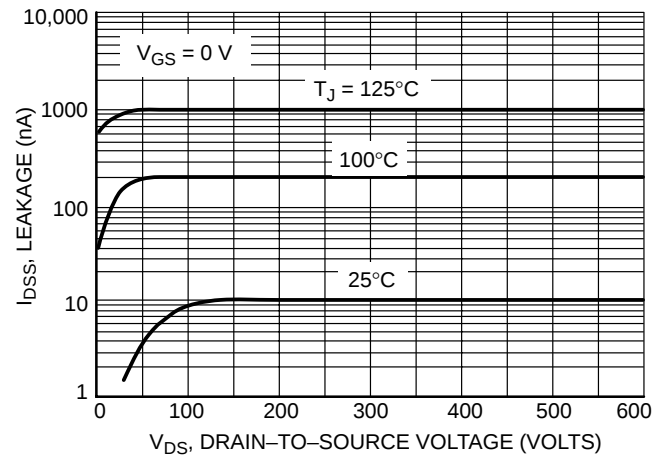


Figure 6. Drain-to-Source Leakage Current versus Voltage

NTP10N60, NTB10N60

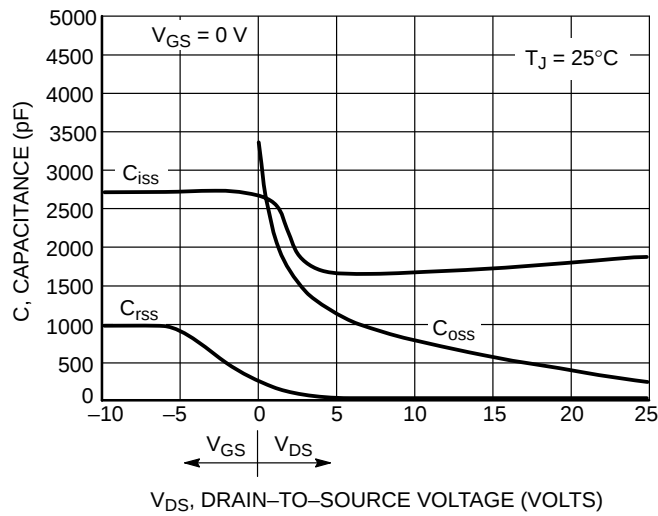


Figure 7. Capacitance Variation

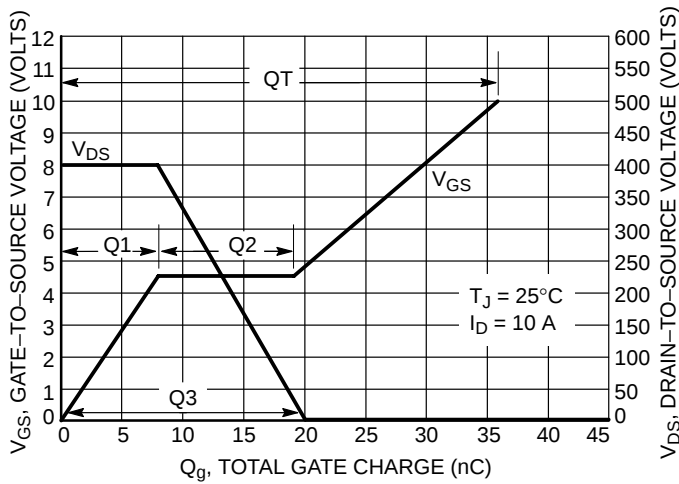


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

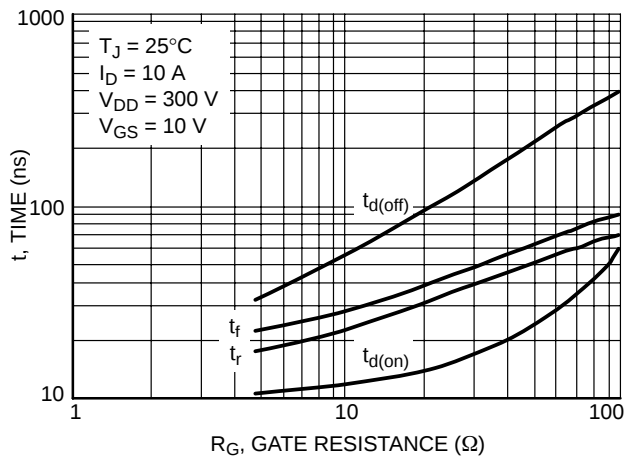


Figure 9. Resistive Switching Time Variation versus Gate Resistance

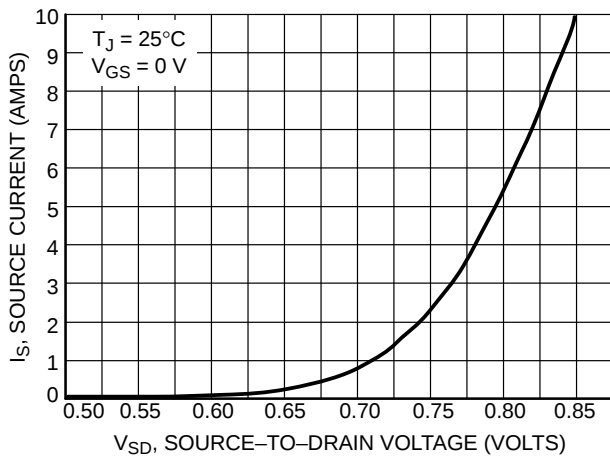


Figure 10. Diode Forward Voltage versus Current

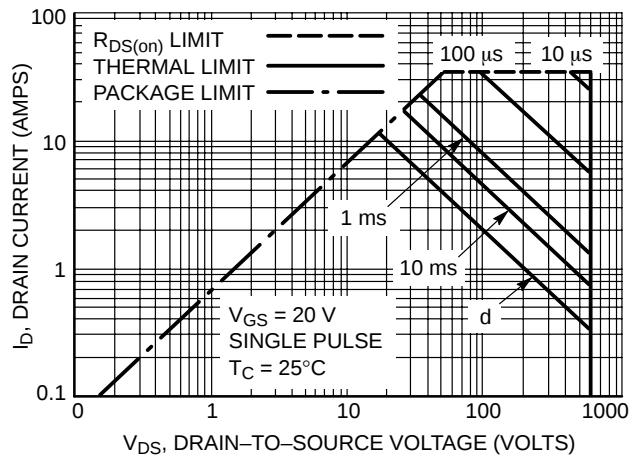


Figure 11. Maximum Rated Forward Biased Safe Operating Area

NTP10N60, NTB10N60

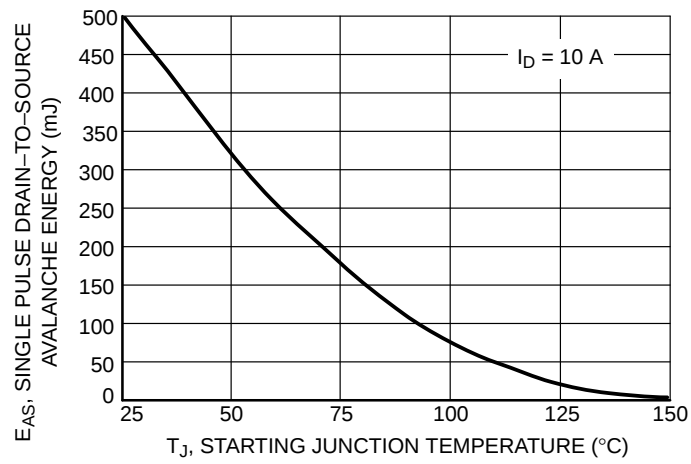


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

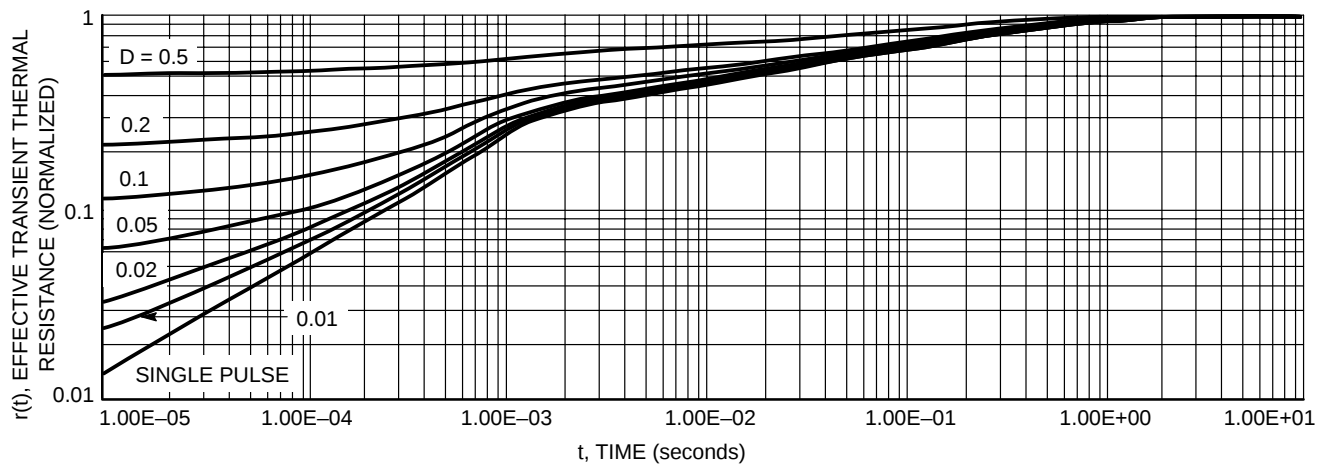
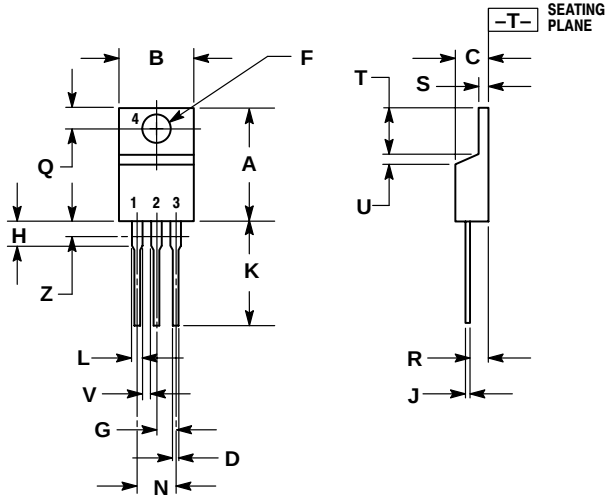


Figure 13. Thermal Response

NTP10N60, NTB10N60

PACKAGE DIMENSIONS

TO-220 THREE-LEAD TO-220AB CASE 221A-09 ISSUE AA



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

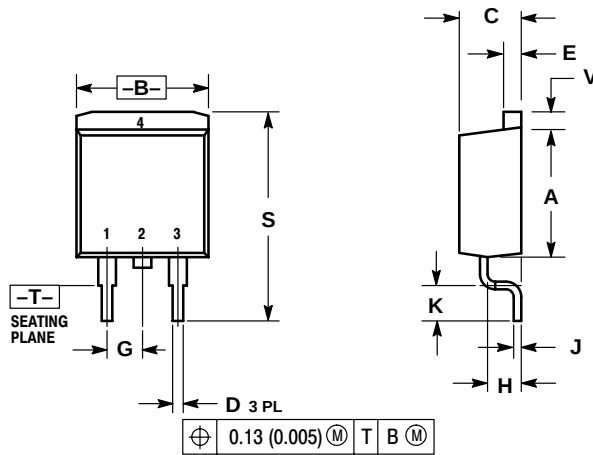
STYLE 5:

- PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

NTP10N60, NTB10N60

PACKAGE DIMENSIONS

D²PAK
CASE 418B-03
ISSUE D



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

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